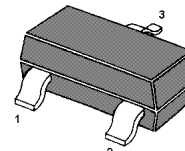
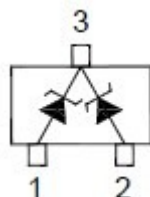


SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE


for general purpose detection and high speed switching applications



Marking Code: **RB**
SOT-23 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

| Parameter | Symbol | Value | Unit |
|--|-----------|---------------|------------------|
| Peak Reverse Voltage | V_{RM} | 40 | V |
| Reverse Voltage | V_R | 40 | V |
| Mean Rectifying Current | I_O | 30 | mA |
| Peak Forward Surge Current ¹⁾ | I_{FSM} | 200 | mA |
| Junction Temperature | T_j | 125 | $^\circ\text{C}$ |
| Storage Temperature Range | T_s | - 40 to + 125 | $^\circ\text{C}$ |

¹⁾ 60 Hz for 1 

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

| Parameter | Symbol | Typ. | Max. | Unit |
|---|--------|------|------|---------------|
| Forward Voltage at $I_F = 1\text{ mA}$ | V_F | - | 0.37 | V |
| Reverse Current at $V_R = 10\text{ V}$ | I_R | - | 1 | μA |
| Capacitance between Terminals at $V_R = 1\text{ V}$, $f = 1\text{ MHz}$ | C_T | 2 | - | pF |

Note: ESD sensitive product handling required.

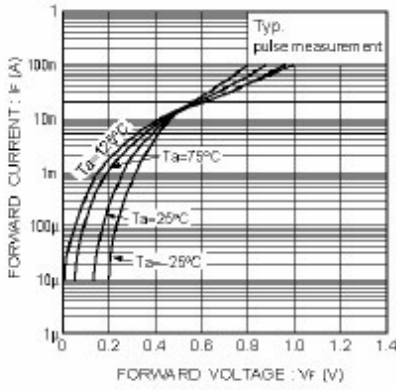


Fig. 1 Forward characteristics

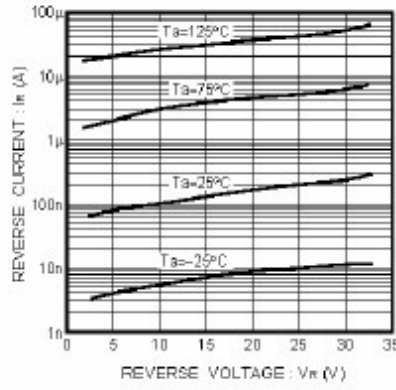


Fig. 2 Reverse characteristics

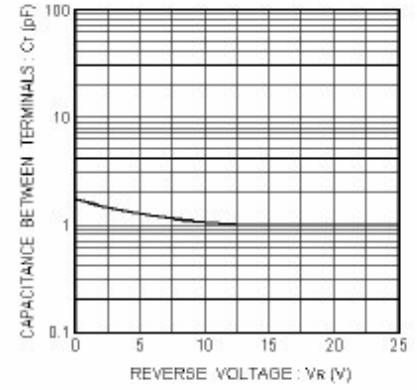


Fig. 3 Capacitance between terminals characteristics

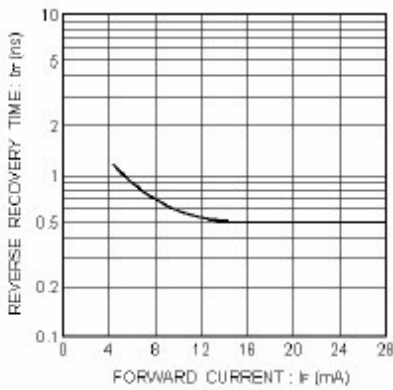


Fig. 4 Reverse recovery time characteristics

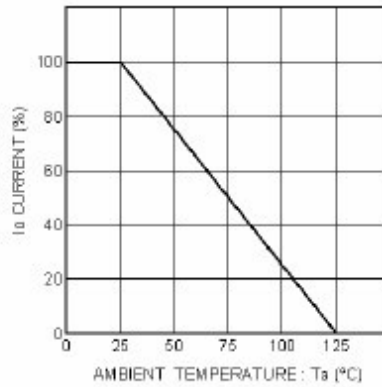


Fig. 5 Derating curve (mounting on glass epoxy PCBs)